IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A semiconductor memory device having a gate insulation film, comprising:

a semiconductor substrate;

a memory cell array formed on the semiconductor substrate, the memory cell array including a plurality of memory cell transistors, each of which has the gate insulation film;

a first interlayer insulation film covering ~~covered~~ the memory cell array and including deuterium;

a silicon nitride layer formed above the first interlayer insulation film; and

a second interlayer insulation film formed above the silicon nitride layer[[,]] and including deuterium, a density of deuterium in the first interlayer insulation film being higher than that of deuterium in the second interlayer insulation film.

Claim 2 (Currently Amended): The semiconductor memory device having a gate insulation film according to claim 1, wherein the gate insulation film is a tunnel oxide film.

Claim 3 (Original): The semiconductor memory device having a gate insulation film according to claim 1, further comprising a conductive line formed on the second interlayer insulation film.

Claim 4 (Currently Amended): The semiconductor memory device having a gate insulation film according to claim 1, wherein the semiconductor memory device is a nonvolatile memory device.

Claim 5 (Currently Amended): The semiconductor memory device having a gate insulation film according to claim 1, wherein the semiconductor memory device includes one of a NAND type, an AND type, a NOR type, and a DINOR type ~~types~~ of a nonvolatile memory device.

Claim 6 (Original): A memory card including the semiconductor memory device recited in claim 1.

Claim 7 (Original): A card holder to which the memory card recited in claim 6 is inserted.

Claim 8 (Original): A connecting device to which the memory card recited in claim 6 is inserted.

Claim 9 (Currently Amended): The connecting device according to the claim 8, wherein the connecting device is configured to be connected to a computer.

Claim 10 (Original): A memory card including the semiconductor memory device recited in claim 1 and a controller which controls the semiconductor memory device.

Claim 11 (Original): A card holder to which the memory card recited in claim 10 is inserted.

Claim 12 (Original): A connecting device to which the memory card recited in claim 10 is inserted.

Claim 13 (Currently Amended): The connecting device according to the claim 12, wherein the connecting device is configured to be connected to a computer.

Claim 14 (Original): An IC card on which an IC chip that includes the semiconductor memory device recited in claim 1 is located.

Claim 15 (Currently Amended): A semiconductor memory device having a gate insulation film, comprising:

a semiconductor substrate;

a memory cell array formed on the semiconductor substrate, the memory cell array including a plurality of memory cell transistors, each of which has the gate insulation film, a floating gate formed on the gate insulating film, and a control gate adjacent to the floating gate;

a first interlayer insulation film covering ~~covered~~ the memory cell array and including deuterium;

a silicon nitride layer formed above the first interlayer insulation film;

a second interlayer insulation film formed above the silicon nitride layer[[,]] and including deuterium, a density of deuterium in the first interlayer insulation film being higher than that of deuterium in the second interlayer insulation film; and

a bit line formed above the second interlayer insulation film.

Claim 16 (Currently Amended): The semiconductor memory device having a gate insulation film according to claim 15, wherein the gate insulation film is a tunnel oxide film.

Claim 17 (Original): The semiconductor memory device having a gate insulation film according to claim 15, further comprising a conductive line formed on the second interlayer insulation film.

Claim 18 (Currently Amended): The semiconductor memory device having a gate insulation film according to claim 15, wherein the semiconductor memory device is a nonvolatile memory device.

Claim 19 (Original): A memory card including the semiconductor memory device recited in claim 15.

Claim 20 (Original): A card holder to which the memory card recited in claim 19 is inserted.

Claim 21 (Original): A connecting device to which the memory card recited in claim 19 is inserted.

Claim 22 (Currently Amended): The connecting device according to the claim 21, wherein the connecting device is configured to be connected to a computer.

Claim 23 (Original): A memory card including the semiconductor memory device recited in claim 15 and a controller which controls the semiconductor memory device.

Claim 24 (Original): A card holder to which the memory card recited in claim 23 is inserted.

Claim 25 (Original): A connecting device to which the memory card recited in claim 23 is inserted.

Claim 26 (Currently Amended): The connecting device according to the claim 25, wherein the connecting device is configured to be connected to a computer.

Claim 27 (Original): An IC card on which an IC chip that includes the semiconductor memory device recited in claim 15 is located.

Claim 28 (Currently Amended): The semiconductor memory device having a gate insulation film according to claim 15, wherein the semiconductor memory device includes one of a NAND type, an AND type, a NOR type, and a DINOR type ~~types~~ of a nonvolatile memory device.

Claims 29-33 (Canceled).